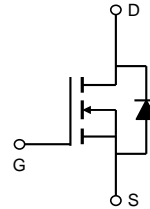


General Description

The AOD4454 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for boost converters and synchronous rectifiers for consumer, telecom, industrial power supplies and LED backlighting.

Features

V_{DS}	150V
I_D (at $V_{GS}=10V$)	20A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 94m Ω
$R_{DS(ON)}$ (at $V_{GS}=7V$)	< 110m Ω



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	20
		$T_C=100^\circ\text{C}$	14
Pulsed Drain Current ^C	I_{DM}	40	A
Continuous Drain Current	I_{DSM}	$T_A=25^\circ\text{C}$	3
		$T_A=70^\circ\text{C}$	2.5
Avalanche Current ^C	I_{AS}, I_{AR}	5	A
Avalanche energy $L=0.1\text{mH}$ ^C	E_{AS}, E_{AR}	1.3	mJ
Power Dissipation ^B	P_D	$T_C=25^\circ\text{C}$	100
		$T_C=100^\circ\text{C}$	50
Power Dissipation ^A	P_{DSM}	$T_A=25^\circ\text{C}$	2.5
		$T_A=70^\circ\text{C}$	1.6
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	16	20	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Ambient ^{A D}		Steady-State	41	50
Maximum Junction-to-Case	$R_{\theta JC}$	1.2	1.5	$^\circ\text{C}/\text{W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
STATIC PARAMETERS							
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	150			V	
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =150V, V _{GS} =0V T _J =55°C			1 5	μA	
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			±100	nA	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	3.4	4	4.6	V	
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	40			A	
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =10A T _J =125°C		75.5 151	94 188	mΩ	
		V _{GS} =7V, I _D =10A		84	110		
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =10A		20		S	
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.72	1	V	
I _S	Maximum Body-Diode Continuous Current ^G				46	A	
DYNAMIC PARAMETERS							
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =75V, f=1MHz	655	820	985	pF	
C _{oss}	Output Capacitance		50	70	90	pF	
C _{rss}	Reverse Transfer Capacitance		13	22	31	pF	
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.7	1.4	2.1	Ω	
SWITCHING PARAMETERS							
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =75V, I _D =10A	10	15	20	nC	
Q _{gs}	Gate Source Charge				4		nC
Q _{gd}	Gate Drain Charge				4.4		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =75V, R _L =7.5Ω, R _{GEN} =3Ω		10.5		ns	
t _r	Turn-On Rise Time			5.5		ns	
t _{D(off)}	Turn-Off DelayTime			14.5		ns	
t _f	Turn-Off Fall Time			3		ns	
t _{rr}	Body Diode Reverse Recovery Time	I _F =10A, dI/dt=500A/μs	20	32.5	45	ns	
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =10A, dI/dt=500A/μs	160	230	300	nC	

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The Power dissipation P_{DSM} is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allow s it.

B. The power dissipation P_D is based on T_{J(MAX)}=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=175°C. Ratings are based on low frequency and duty cycles to keep initial T_J=25°C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175°C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

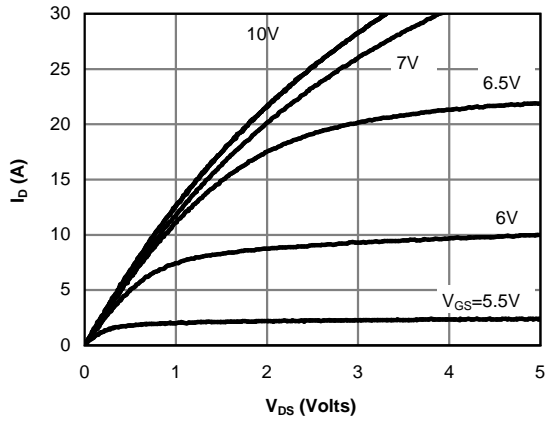


Fig 1: On-Region Characteristics (Note E)

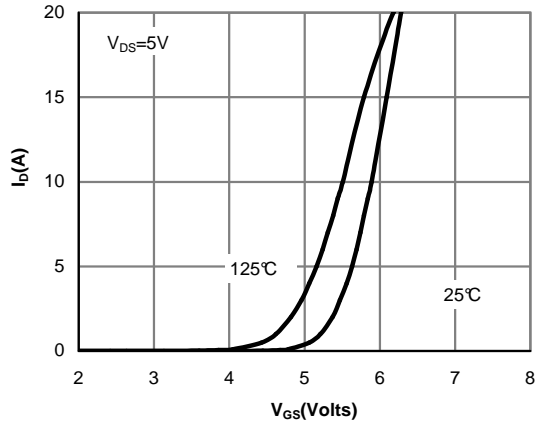


Figure 2: Transfer Characteristics (Note E)

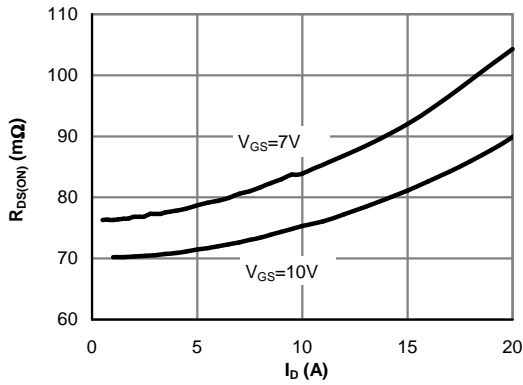


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

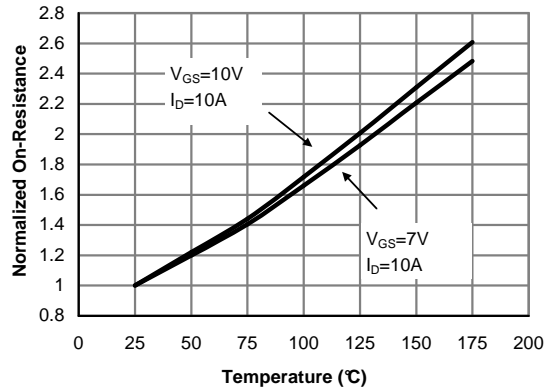


Figure 4: On-Resistance vs. Junction Temperature (Note E)

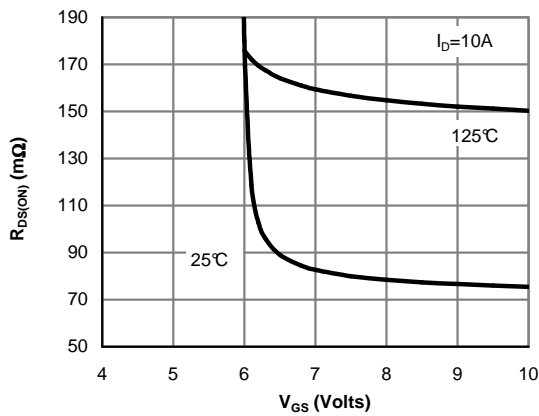


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

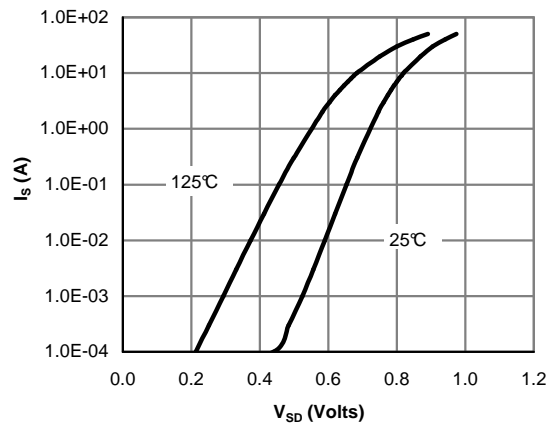


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

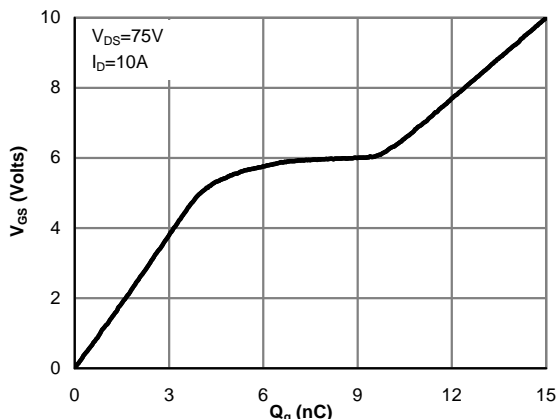


Figure 7: Gate-Charge Characteristics

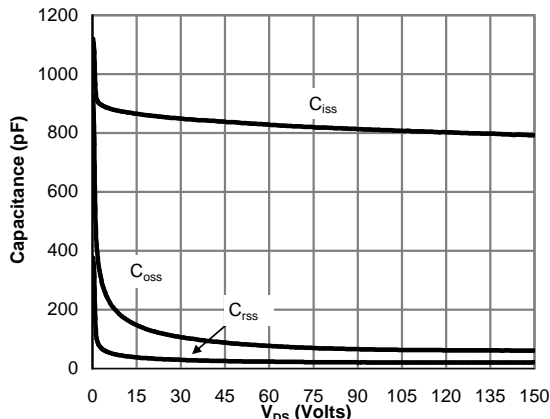


Figure 8: Capacitance Characteristics

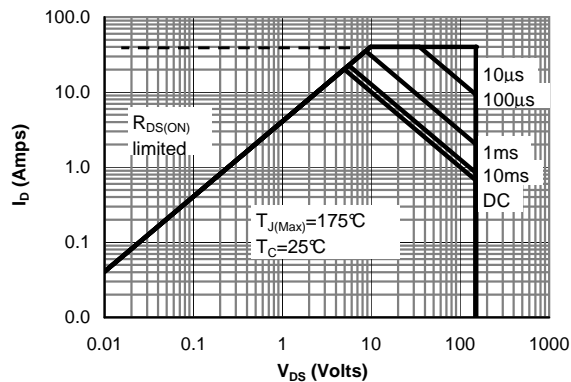


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

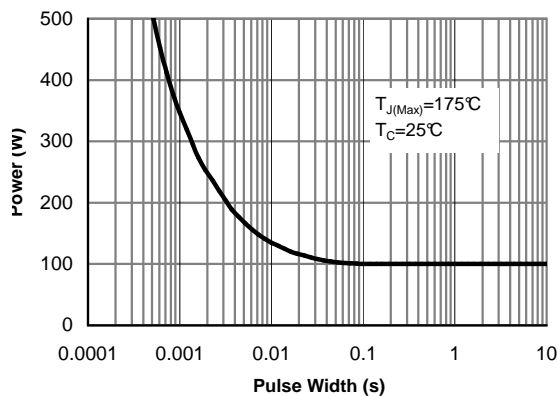


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

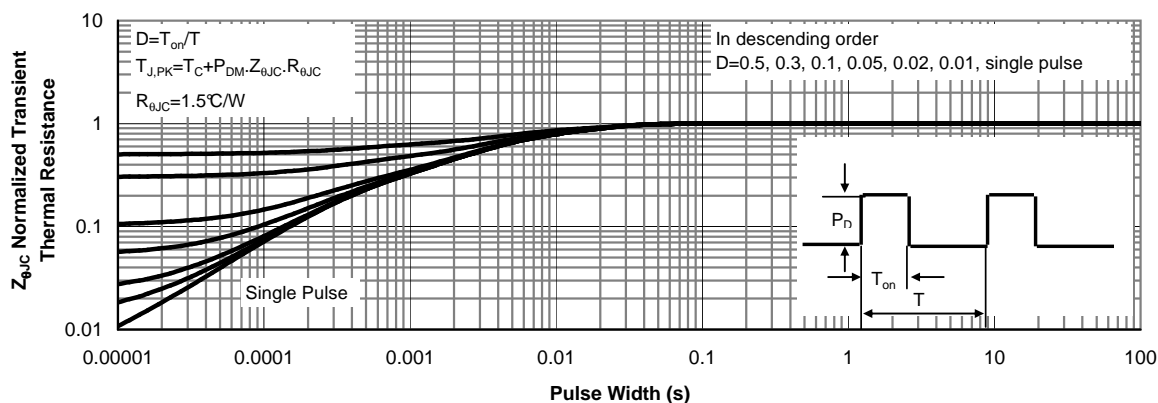


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

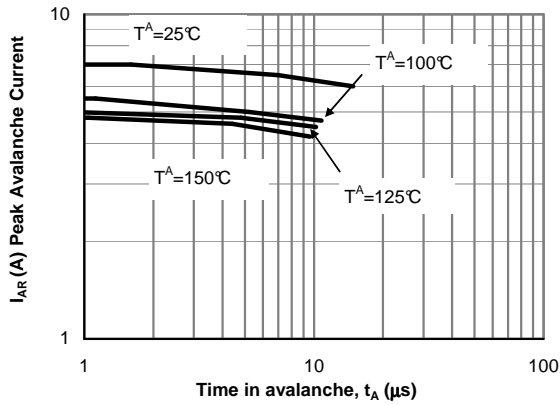


Figure 12: Single Pulse Avalanche capability (Note C)

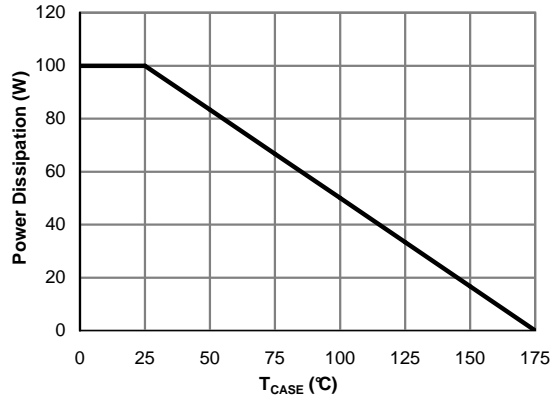


Figure 13: Power De-rating (Note F)

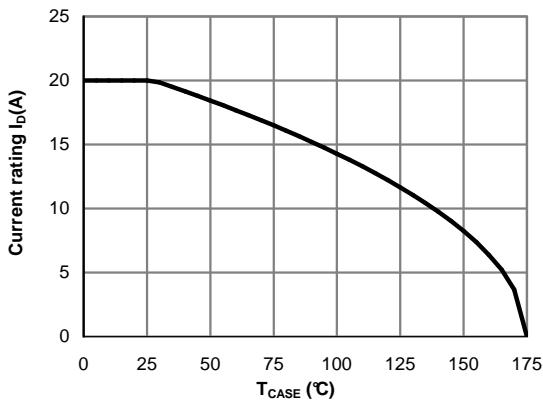


Figure 14: Current De-rating (Note F)

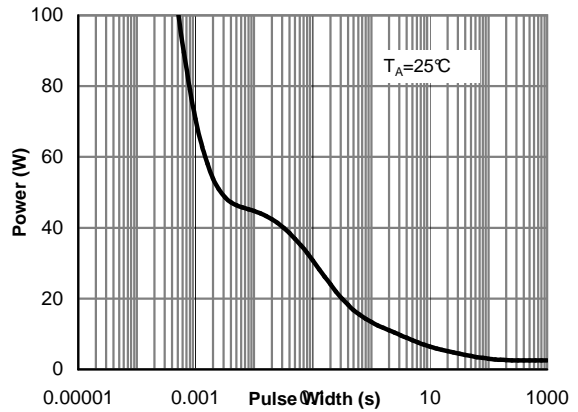


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

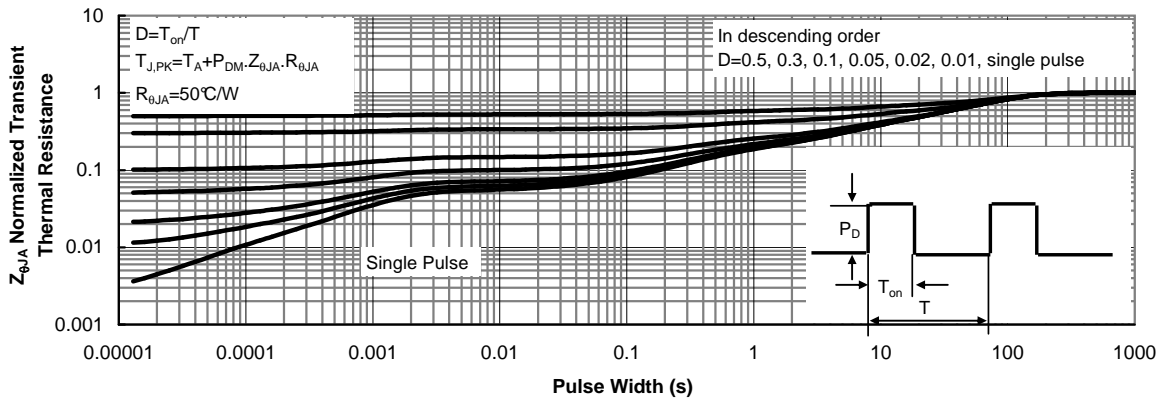
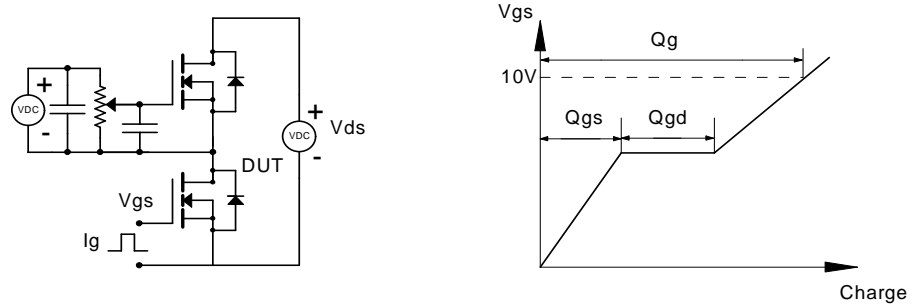
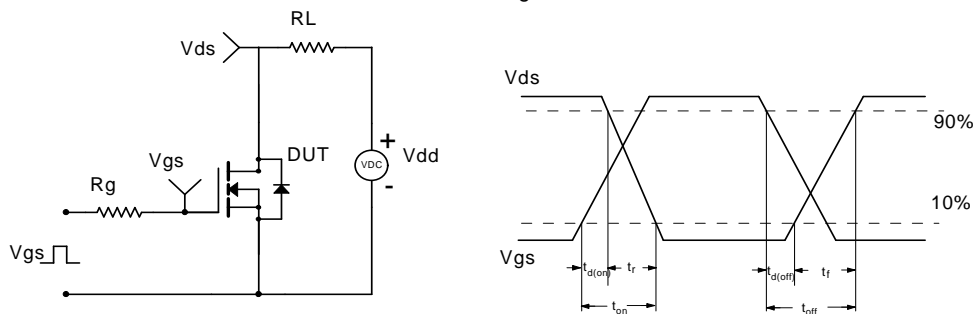


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

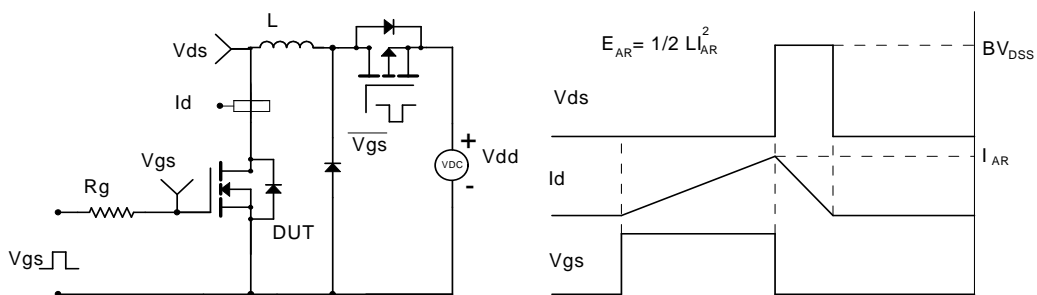
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

